

REMARKS

Claim 1 has been amended to emphasize that a feature of the invention is the creation of a set of transistors that have a highly uniform gate length, providing greater uniformity than is possible by lithographic techniques.

Support is provided by paragraphs 27, 33 and 46.

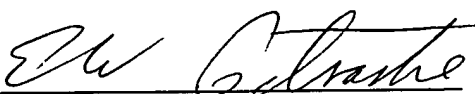
Paragraphs 27 and 46 in the specification have been amended to provide support for the new claim language. Since the change relates only to labels used in the claims, no new matter has been added.

The Roesner reference does refer to the gate as controlling the conductivity of the channel, but does not refer to the benefit of using advanced polishing techniques to provide a high degree of uniformity, within a small tolerance, on the thickness of the gate layer.

There is thus no teaching in Roesner that improved circuit operation may be obtained by going to the extra expense of providing a high degree of uniformity on the thickness of the gate layer.

For the foregoing reasons, allowance of the claims is respectfully
solicited.

Respectfully submitted,

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